

Before considering the application, please amend the application as follows.

IN THE CLAIMS

Please cancel claims 26 and 38, and amend claims 16 and 28 as follows:

16. (Twice Amended) An integrated circuit comprising:

a plurality of metal layers comprising a plurality of conductors to interconnect components in an integrated circuit, said metal layers comprising:

(1) a first metal layer group comprising at least one metal layer, said metal layer in said first metal layer group comprising at least one self contained layout section comprising conductors deposited in a preferred Manhattan direction, wherein a preferred direction defines a direction, relative to the integrated circuit boundaries, for at least fifty percent of conductors, and said self contained layout section comprising a routing of conductors developed independent from routing of conductors for circuits outside said self contained layout section in said integrated circuit; and

a second metal layer group comprising at least one metal layer, said metal layer in said second metal layer group comprising a plurality of conductors deposited in a preferred diagonal direction in a portion of the metal layer directly adjacent to said portion of said metal layer for said self contained layout section, and wherein conductors for said second metal layer group are routed independent from routing of conductors for said self contained layout section,

C1
whereby said preferred Manhattan direction conductors of said self contained layer within said first metal group do not electrically cross-couple with conductors of said second metal layer group regardless of whether said self contained layout conductors are deposited in either a horizontal or vertical direction.

28. (Twice Amended) A method for depositing a plurality of metal layers comprising a plurality of conductors to interconnect components of an integrated circuit, said method comprising the steps of:

C2
designating a first metal layer group comprising at least one metal layer, said metal layer in said first metal layer group comprising at least one self contained layout section comprising conductors deposited in a preferred Manhattan direction, wherein a preferred direction defines a direction, relative to the integrated circuit boundaries, for at least fifty percent of conductors and said self contained layout section comprising a routing of conductors developed independent from routing of conductors for circuits outside said self contained layout section in said integrated circuit; and

designating a second metal layer group comprising at least one metal layer, said metal layer in said second metal layer group comprising a plurality of conductors deposited in a preferred diagonal direction in a portion of the metal layer directly adjacent to said portion of said metal layer for said self contained layout, and wherein conductors for said second metal layer group are routed independent from routing of conductors for said self contained layout section,